

DMTH6005LFG

### 60V +175°C N-CHANNEL ENHANCEMENT MODE MOSFET PowerDI3333-8

### **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> Max	I <sub>D</sub> Max T <sub>C</sub> = +25°C (Note 9)
	4.1mΩ @ V <sub>GS</sub> = 10V	100A
60V	6.3mΩ @ V <sub>GS</sub> = 6V	89A
	7mΩ @ V <sub>GS</sub> = 4.5V	84A

# **Description and Applications**

This MOSFET is designed to minimize the on-state resistance (RDS(ON)), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Synchronous Rectification
- Motor Control
- **DC-DC Converters**
- Power Management

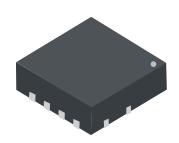
### **Features and Benefits**

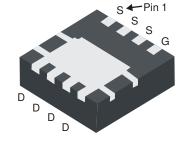
- Rated to +175°C Ideal for High Ambient Temperature Environments
- 100% Unclamped Inductive Switching(UIS) Test in Production -Ensures More Reliable And Robust End Application
- Low R<sub>DS(ON)</sub> Ensures On-State Losses are Minimized
- Small Form Factor Thermally Efficient Package Enables Higher **Density End Products**
- Occupies Just 33% of the Board Area Occupied by SO-8 Enabling Smaller End Product
- Lead-Free Finish: RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- For automotive applications requiring specific change control (i.e. parts qualified to AEC-Q100/101/200, PPAP capable, and manufactured in IATF 16949 certified facilities), please contact us or your local Diodes representative. https://www.diodes.com/quality/product-definitions/

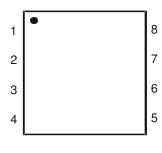
#### **Mechanical Data**

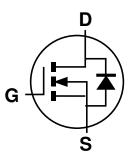
- Case: PowerDI®3333-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 @3
- Weight: 0.029 grams (Approximate)

#### PowerDI3333-8









Top View

**Bottom View** 

Top View

**Equivalent Circuit** 

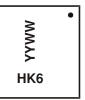
### Ordering Information (Note 4)

Part Number	Case	Packaging
DMTH6005LFG-7	PowerDI3333-8	2,000/Tape & Reel
DMTH6005LFG-13	PowerDI3333-8	3,000/Tape & Reel

Notes:

- 1. EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant. All applicable RoHS exemptions applied.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



HK6 = Product Type Marking Code YYWW = Date Code Marking YY = Last Two Digits of Year (ex: 20 = 2020) WW = Week Code (01 to 53)

March 2020



# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V <sub>DSS</sub>	60	V	
Gate-Source Voltage	Vgss	±20	V	
Continuous Drain Current (Notes 6 & 9) V <sub>GS</sub> = 10V	T <sub>C</sub> = +25°C T <sub>C</sub> = +100°C	lo	100 78	А
Continuous Drain Current (Note 5) V <sub>GS</sub> = 10V	$T_A = +25^{\circ}C$ $T_A = +100^{\circ}C$	lo	19.7 13.9	А
Maximum Continuous Body Diode Forward Current (Notes 6 &	Is	100	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	Ірм	400	A	
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle =	Іѕм	400	Α	
Avalanche Current, L=1mH	I <sub>AS</sub>	18.5	Α	
Avalanche Energy, L=1mH	Eas	171	mJ	

# **Thermal Characteristics**

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)	T <sub>A</sub> = +25°C	PD	2.38	W
Thermal Resistance, Junction to Ambient (Note 5)		Reja	63	°C/W
Total Power Dissipation (Note 6) $T_C = +25^{\circ}C$		PD	75	W
Thermal Resistance, Junction to Case (Note 6)		Rejc	2.0	°C/W
Operating and Storage Temperature Range	TJ, TSTG	-55 to +175	°C	

### **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

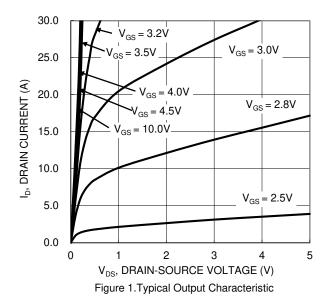
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	60	_	_	V	$V_{GS} = 0V$ , $I_D = 1mA$
Zero Gate Voltage Drain Current		_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$
Gate-Source Leakage	Igss	_	_	±100	nA	$V_{GS} = \pm 20V$ , $V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	1		2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$
	R <sub>DS(ON)</sub>	_	3.1	4.1	mΩ	V <sub>GS</sub> = 10V, I <sub>D</sub> = 20A
Static Drain-Source On-Resistance		_	3.6	6.3	mΩ	$V_{GS} = 6V$ , $I_D = 5A$
		_	4.4	7	mΩ	$V_{GS} = 4.5V, I_{D} = 5A$
Diode Forward Voltage	VsD	_	0.8	1.2	V	Vgs = 0V, Is = 20A
DYNAMIC CHARACTERISTICS (Note 8)			I.			·
Input Capacitance	Ciss	_	3150	_	рF	V <sub>DS</sub> = 30V, V <sub>GS</sub> = 0V, f = 1MHz
Output Capacitance	Coss	_	1036	_		
Reverse Transfer Capacitance	Crss		69	_		
Gate Resistance	Rg		0.7	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1MHz$
Total Gate Charge (V <sub>GS</sub> = 10V)	Qg	_	48.7	_		
Total Gate Charge (VGS = 4.5V)	Qg		23.6	_	nC	$V_{DD} = 30V, I_D = 50A$
Gate-Source Charge	Qgs	_	7.0	_		
Gate-Drain Charge	Qgd		11.2	_		
Turn-On Delay Time	t <sub>D(ON)</sub>	_	7.3	_		$V_{DD} = 30V, V_{GS} = 10V,$ $I_{D} = 30A, R_{G} = 3.3\Omega$
Turn-On Rise Time	t <sub>R</sub>		11.3	_	ns	
Turn-Off Delay Time	tD(OFF)	_	26.0	_		
Turn-Off Fall Time	t <sub>F</sub>	_	11.0	_		
Body Diode Reverse Recovery Time	trr	_	40.8	_	ns	1 004 31/34 4004/55
Body Diode Reverse Recovery Charge	Qrr	_	51.5	_	nC	IF = 30A, di/dt = 100A/μs

5. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate. Notes:

6. Thermal resistance from junction to soldering point (on the exposed drain pad).

7. Short duration pulse test used to minimize self-heating effect.8. Guaranteed by design. Not subject to product testing.9. Limited by Package.





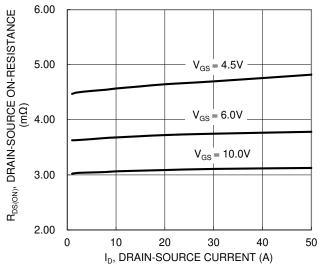


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

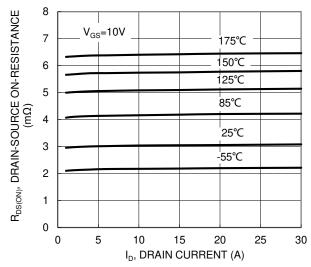


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

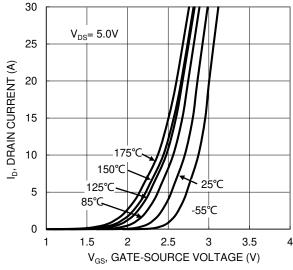
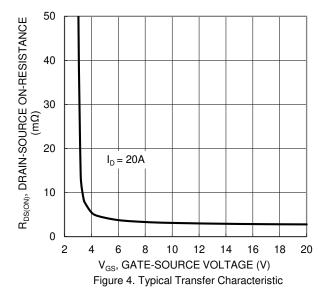


Figure 2. Typical Transfer Characteristic



2.2  $V_{GS} = 10V, I_D = 20A$ R<sub>DS(ON)</sub>, DRAIN-SOURCE ON-RESISTANCE (NORMALIZED) 2  $V_{GS} = 6.0V, I_D = 5A$ 1.8 1.6 1.4 1.2  $V_{GS} = 4.5V, I_{D} = 5A$ 1 8.0 0.6 -50 -25 0 50 75 25 100 125 150 175 T<sub>J</sub>, JUNCTION TEMPERATURE (°C)

Figure 6. On-Resistance Variation with Temperature



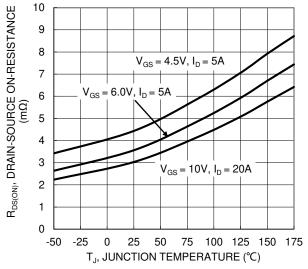


Figure 7. On-Resistance Variation with Temperature

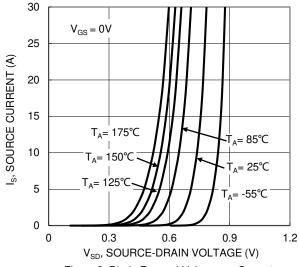


Figure 9. Diode Forward Voltage vs. Current

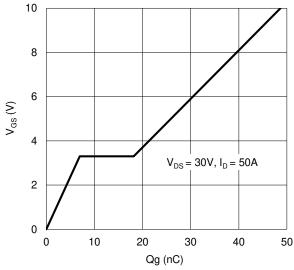


Figure 11. Gate Charge

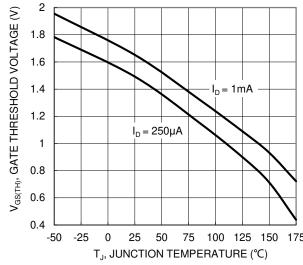
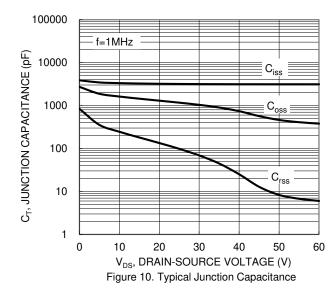
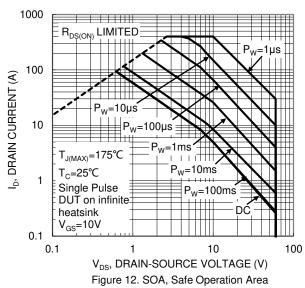


Figure 8. Gate Threshold Variation vs. JunctionTemperature







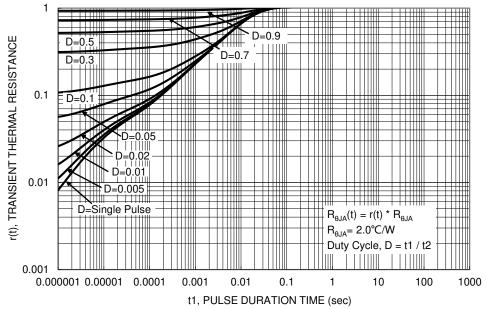


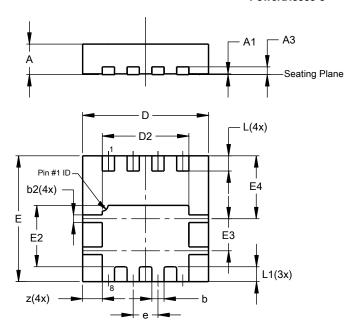
Figure 13. Transient Thermal Resistance



# **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

#### PowerDI3333-8

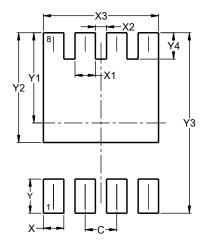


PowerDI3333-8					
Dim	Min	Max	Тур		
Α	0.75	0.85	0.80		
A1	0.00	0.05	0.02		
<b>A</b> 3	-	-	0.203		
b	0.27	0.37	0.32		
b2	0.15	0.25	0.20		
D	3.25	3.35	3.30		
D2	2.22	2.32	2.27		
E	3.25	3.35	3.30		
E2	1.56	1.66	1.61		
E3	0.79	0.89	0.84		
E4	1.60	1.70	1.65		
е	_	_	0.65		
L	0.35	0.45	0.40		
L1	_	_	0.39		
Z	_	_	0.515		
All Dimensions in mm					

# **Suggested Pad Layout**

 $Please see \ http://www.diodes.com/package-outlines.html \ for \ the \ latest \ version.$ 

#### PowerDI3333-8



Dimensions	value (in mm)
C	0.650
X	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700
Y4	0.540



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